Abdulmecit Turut

List of Publications by Year
in descending order

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247	8,379	41258	76769
papers	citations	49 h-index	74 g-index

250	250	250	2758
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Temperature dependence of characteristic parameters of the H-terminated Sn/p-Si(1 0 0) Schottky contacts. Applied Surface Science, 2003, 217, 250-260.	3.1	243
2	Temperature dependent barrier characteristics of CrNiCo alloy Schottky contacts on n-type molecular-beam epitaxy GaAs. Journal of Applied Physics, 2002, 91, 245.	1.1	227
3	Electrical characterization of Au/n-ZnO Schottky contacts on n-Si. Journal of Alloys and Compounds, 2009, 476, 913-918.	2.8	168
4	The electrical modulus and other dielectric properties by the impedance spectroscopy of LaCrO₃ and LaCr_{0.90}Ir_{0.10}O₃ perovskites. RSC Advances, 2018, 8, 4634-4648.	1.7	167
5	Interpreting the nonideal reverse bias C-V characteristics and importance of the dependence of Schottky barrier height on applied voltage. Physica B: Condensed Matter, 1995, 205, 41-50.	1.3	150
6	Parameter extraction from non-ideal Câ^'V characteristics of a Schottky diode with and without interfacial layer. Solid-State Electronics, 1992, 35, 835-841.	0.8	148
7	Fabrication and electrical characteristics of Schottky diode based on organic material. Microelectronic Engineering, 2008, 85, 1647-1651.	1.1	144
8	The determination of interface state energy distribution of the H-terminated Zn/p-type Si Schottky diodes with high series resistance by the admittance spectroscopy. Vacuum, 2004, 74, 45-53.	1.6	122
9	The electrical characteristics of Sn/methyl-red/p-type Si/Al contacts. Microelectronic Engineering, 2007, 84, 2875-2882.	1.1	117
10	Electrical transport characteristics of Sn/p-Si schottky contacts revealed from Iâ€“Vâ€“T and Câ€“Vâ€“T measurements. Physica B: Condensed Matter, 2007, 392, 43-50.	1.3	117
11	Current-voltage and capacitance-voltage characteristics of Sn/rhodamine-101â^•n-Si and Sn/rhodamine-101â^•p-Si Schottky barrier diodes. Journal of Applied Physics, 2006, 100, 074505.	1.1	108
12	Capacitanceâ€“conductanceâ€“currentâ€“voltage characteristics of atomic layer deposited Au/Ti/Al2O3/n-GaAs MIS structures. Materials Science in Semiconductor Processing, 2015, 39, 400-407.	1.9	108
13	On temperature-dependent experimental I-V and C-V data of Ni/n-GaN Schottky contacts. Journal of Applied Physics, 2010, 108, .	1.1	104
14	The nonpolymeric organic compound (pyronine-B)/p-type silicon/Sn contact barrier devices. Synthetic Metals, 2002, 126, 213-218.	2.1	101
15	On the barrier inhomogeneities of polyaniline/p-Si/Al structure at low temperature. Applied Surface Science, 2005, 250, 43-49.	3.1	98
16	Some electrical properties of polyaniline/p-Si/Al structure at 300K and 77K temperatures. Microelectronic Engineering, 2008, 85, 278-283.	1.1	97
17	The bias-dependence change of barrier height of Schottky diodes under forward bias by including the series resistance effect. Physica Scripta, 1996, 53, 118-122.	1.2	93
18	Currentâ€“voltage and capacitanceâ€“voltage characteristics of polypyrrole/p-InP structure. Vacuum, 2005, 77, 269-274.	1.6	90

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19	Effect of series resistance on the forward current-voltage characteristics of Schottky diodes in the presence of interfacial layer. Solid-State Electronics, 1996, 39, 83-87.	0.8	89
20	The double Gaussian distribution of barrier heights in Au/n-GaAs Schottky diodes fromIâ€“Vâ€“Tcharacteristics. Semiconductor Science and Technology, 2006, 21, 298-302.	1.0	88
21	Oncurrent-voltage and capacitance-voltage characteristics of metal-semiconductor contacts. Turkish Journal of Physics, 2020, 44, 302-347.	0.5	82
22	The surface morphology properties and respond illumination impact of ZnO/n-Si photodiode by prepared atomic layer deposition technique. Journal of Alloys and Compounds, 2017, 691, 873-879.	2.8	80
23	Semiconductive polymerâ€based Schottky diode. Journal of Applied Physics, 1992, 72, 818-819.	1.1	78
24	The Schottky barrier height of the rectifying Cu/pyronine-B/p-Si, Au/pyronine-B/p-Si, Sn/pyronine-B/p-Si and Al/pyronine-B/p-Si contacts. Synthetic Metals, 2004, 142, 177-180.	2.1	78
25	The effects of the temperature on the some parameters obtained from currentâ€“voltage and capacitanceâ€“voltage characteristics of polypyrrole/n-Si structure. Polymer, 2005, 46, 563-568.	1.8	77
26	Determination of the density of Si-metal interface states and excess capacitance caused by them. Physica B: Condensed Matter, 1992, 179, 285-294.	1.3	75
27	Temperature-dependent behavior of Ni/4H-nSiC Schottky contacts. Journal of Applied Physics, 2007, 102, 043701.	1.1	75
28	Temperature dependent current-transport mechanism in Au/(Zn-doped)PVA/n-GaAs Schottky barrier diodes (SBDs). Sensors and Actuators A: Physical, 2013, 199, 194-201.	2.0	74
29	The effect of Schottky metal thickness on barrier height inhomogeneity in identically prepared Au/n-GaAs Schottky diodes. Semiconductor Science and Technology, 2006, 21, 1-5.	1.0	71
30	The energy distribution of the interface state density of Pb/p-Si Schottky contacts exposed to clean room air. Applied Surface Science, 2003, 207, 190-199.	3.1	68
31	Engineering the band gap of LaCrO3 doping with transition metals (Co, Pd, and Ir). Journal of Materials Science, 2018, 53, 3544-3556.	1.7	68
32	Series resistance calculation for the Metal-Insulator-Semiconductor Schottky barrier diodes. Applied Physics A: Materials Science and Processing, 1996, 62, 269-273.	1.1	64
33	Temperature dependence of the currentâ€“voltage characteristics of the Al/Rhodamine-101/p-Si(100) contacts. Applied Surface Science, 2006, 252, 2209-2216.	3.1	64
34	High barrier Schottky diode with organic interlayer. Solid State Communications, 2012, 152, 381-385.	0.9	64
35	The conductance and capacitanceâ€“frequency characteristics of Au/pyronine-B/p-type Si/Al contacts. Applied Surface Science, 2007, 253, 3464-3468.	3.1	63
36	High barrier metallic polymer/p-type silicon Schottky diodes. Solid-State Electronics, 1996, 39, 677-680.	0.8	61

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37	Laterally inhomogeneous barrier analysis of the methyl violet/p-Si organic/inorganic hybrid Schottky structures. Applied Surface Science, 2008, 254, 3039-3044.	3.1	61
38	The determination of electronic and interface state density distributions of Au/n-type GaAs Schottky barrier diodes. Physica B: Condensed Matter, 2006, 381, 199-203.	1.3	60
39	Electrical properties and interface state energy distributions of Cr/n-Si Schottky barrier diode. Superlattices and Microstructures, 2013, 64, 483-494.	1.4	60
40	On the Forward Bias Excess Capacitance at Intimate and MIS Schottky Barrier Diodes with Perfect or Imperfect Ohmic Back Contact. Physica Scripta, 2000, 61, 209-212.	1.2	58
41	Series resistance determination of Au/Polypyrrole/p-Si/Al structure by currentâ€“voltage measurements at low temperatures. Materials Science and Engineering C, 2009, 29, 1486-1490.	3.8	57
42	Electrical analysis of organic dye-based MIS Schottky contacts. Microelectronic Engineering, 2010, 87, 2482-2487.	1.1	57
43	Ti/p-Si Schottky barrier diodes with interfacial layer prepared by thermal oxidation. Physica B: Condensed Matter, 2005, 364, 133-141.	1.3	55
44	Effect of 6MeV electron irradiation on electrical characteristics of the Au/n-Si/Al Schottky diode. Microelectronic Engineering, 2008, 85, 2299-2303.	1.1	55
45	Temperature dependent Iâ€“V characteristics of an Au/n-GaAs Schottky diode analyzed using Tungâ€™s model. Physica B: Condensed Matter, 2013, 414, 35-41.	1.3	55
46	Electrical analysis of organic interlayer based metal/interlayer/semiconductor diode structures. Journal of Applied Physics, 2009, 106, .	1.1	54
47	Os doped YMnO3 multiferroic: A study investigating the electrical properties through tuning the doping level. Journal of Alloys and Compounds, 2018, 752, 274-288.	2.8	54
48	Currentâ€“voltage characteristics of Al/Rhodamine-101/n-GaAs structures in the wide temperature range. Current Applied Physics, 2010, 10, 761-765.	1.1	53
49	Temperature dependent negative capacitance behavior of Al/rhodamine-101/n-GaAs Schottky barrier diodes and Rs effects on the Câ€“V and G/Ï‰â€“V characteristics. Journal of Alloys and Compounds, 2012, 513, 107-111.	2.8	53
50	The determination of the interface-state density distribution from the capacitance-frequency measurements in Au/n-Si schottky barrier diodes. Journal of Electronic Materials, 2002, 31, 119-123.	1.0	51
51	The photovoltaic impact of atomic layer deposited TiO 2 interfacial layer on Si-based photodiodes. Solid-State Electronics, 2018, 144, 39-48.	0.8	51
52	Temperature-dependent currentâ€“voltage characteristics of the Au/n-InP diodes with inhomogeneous Schottky barrier height. Physica B: Condensed Matter, 2009, 404, 1558-1562.	1.3	49
53	Electrical characterization of the Al/new fuchsin/n-Si organic-modified device. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 1411-1416.	1.3	49
54	Electronic properties of the metal/organic interlayer/inorganic semiconductor sandwich device. Journal of Physics and Chemistry of Solids, 2010, 71, 351-356.	1.9	47

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55	Temperature dependence of current-voltage characteristics in highly doped Ag/p-GaN/In Schottky diodes. Journal of Applied Physics, 2009, 106, .	1.1	46
56	The conductance and capacitanceâ€“frequency characteristics of the organic compound (pyronine-B)/p-Si structures. Synthetic Metals, 2003, 138, 549-554.	2.1	45
57	Experimental determination of the laterally homogeneous barrier height of Au/n-Si Schottky barrier diodes. Physica B: Condensed Matter, 2004, 348, 397-403.	1.3	44
58	The temperature dependence of currentâ€“voltage characteristics of the Au/Polypyrrole/p-Si/Al heterojunctions. Journal of Physics Condensed Matter, 2006, 18, 2665-2676.	0.7	44
59	Temperature-dependent optical absorption measurements and Schottky contact behavior in layered semiconductor n-type InSe(:Sn). Applied Surface Science, 2007, 253, 3899-3905.	3.1	44
60	Extraction of electronic parameters of Schottky diode based on an organic Orcein. Microelectronic Engineering, 2010, 87, 2525-2530.	1.1	44
61	Temperature dependent currentâ€“voltage and capacitanceâ€“voltage characteristics of chromium Schottky contacts formed by electrodeposition technique on n-type Si. Journal of Alloys and Compounds, 2011, 509, 6433-6439.	2.8	44
62	High-barrier height Sn/p-Si schottky diodes with interfacial layer by anodization process. Applied Surface Science, 2001, 172, 1-7.	3.1	42
63	The frequency-dependent electrical characteristics of interfaces in the Sn/p-Si metal semiconductor structures. Microelectronics Reliability, 2010, 50, 351-355.	0.9	42
64	Influence of Al₂O₃barrier on the interfacial electronic structure of Au/Ti/n-GaAs structures. Journal of Semiconductors, 2017, 38, 054003.	2.0	41
65	The effect of anodic oxide treatment on n-GaAs Schottky barrier diodes. Journal of Materials Science: Materials in Electronics, 2001, 12, 575-579.	1.1	40
66	The electrical and dielectric properties of the Au/Ti/HfO2/n-GaAs structures. Journal of Molecular Structure, 2018, 1157, 513-518.	1.8	39
67	Electronic parameters of high barrier Au/Rhodamine-101/n-Inp Schottky diode with organic Ä±nterlayer. Thin Solid Films, 2012, 520, 1944-1948.	0.8	38
68	Currentâ€“voltage characteristics of Au/ZnO/n-Si device in a wide range temperature. Journal of Materials Science: Materials in Electronics, 2017, 28, 17177-17184.	1.1	38
69	Electronic properties of Al/DNA/p-Si MIS diode: Application as temperature sensor. Journal of Alloys and Compounds, 2011, 509, 571-577.	2.8	37
70	Co doped YbFeO3: exploring the electrical properties via tuning the doping level. Ionics, 2019, 25, 4013-4029.	1.2	36
71	Correlation between barrier heights and ideality factors of Cd/n-Si and Cd/p-Si Schottky barrier diodes. Solid State Communications, 2003, 125, 551-556.	0.9	35
72	Characterization of capacitanceâ€“frequency features of Sn/polypyrrole/n-Si structure as a function of temperature. Polymer, 2005, 46, 6148-6153.	1.8	35

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73	Determination of contact parameters of Au/Carmine/n-Si Schottky device. Thin Solid Films, 2010, 518, 7156-7160.	0.8	35
74	Frequency and temperature dependent electrical and dielectric properties of LaCrO3 and Ir doped LaCrO3 perovskite compounds. Journal of Alloys and Compounds, 2018, 740, 1012-1023.	2.8	35
75	The effects of the time-dependent on the characteristic parameters of polypyrrole/p-type Si/Al diode. Polymer, 2004, 45, 7335-7340.	1.8	34
76	DNA-based organic-on-inorganic semiconductor Schottky structures. Applied Surface Science, 2008, 254, 5175-5180.	3.1	34
77	Examination by interfacial layer and inhomogeneous barrier height model of temperature-dependent Iâ€“V characteristics in Co/p-InP contacts. Journal of Alloys and Compounds, 2009, 484, 870-876.	2.8	34
78	The origin of negative capacitance in Au/n-GaAs Schottky barrier diodes (SBDs) prepared by photolithography technique in the wide frequency range. Current Applied Physics, 2013, 13, 1101-1108.	1.1	34
79	Preparation and characterization of solâ€“gel-derived n-ZnO thin film for Schottky diode application. Applied Physics A: Materials Science and Processing, 2015, 119, 547-552.	1.1	34
80	Effect of thermal annealing in nitrogen on theI - VandC - Vcharacteristics of Cr - Ni - Co alloy/LEC n-GaAs Schottky diodes. Semiconductor Science and Technology, 1997, 12, 1028-1031.	1.0	32
81	Barrier height enhancement in the Au/n-GaAs Schottky diodes with anodization process. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 10.	1.6	32
82	Dependence of characteristic diode parameters on sample temperature in Ni/epitaxy n-Si contacts. Materials Science in Semiconductor Processing, 2011, 14, 5-12.	1.9	32
83	Determination of the lateral barrier height of inhomogeneous Au/n-type InP/In Schottky barrier diodes. Semiconductor Science and Technology, 2007, 22, 851-854.	1.0	31
84	The effects of the temperature and annealing on currentâ€“voltage characteristics of Ni/n-type 6Hâ€“SiC Schottky diode. Microelectronic Engineering, 2008, 85, 631-635.	1.1	31
85	Gamma irradiation-induced changes at the electrical characteristics of organic-based schottky structures. Journal Physics D: Applied Physics, 2008, 41, 135103.	1.3	31
86	Temperature-dependent currentâ€“voltage and capacitanceâ€“voltage characteristics of the Ag/n-InP/In Schottky diodes. Journal of Materials Science: Materials in Electronics, 2009, 20, 105-112.	1.1	31
87	Electrical characterization of Ir doped rare-earth orthoferrite YbFeO3. Journal of Alloys and Compounds, 2019, 787, 1212-1224.	2.8	31
88	The Effect of Series Resistance on the Relationship Between Barrier Heights and Ideality Factors of Inhomogeneous Schottky Barrier Diodes. Physica Scripta, 2004, 70, 364-367.	1.2	30
89	DNA-modified indium phosphide Schottky device. Applied Physics Letters, 2008, 92, 212106.	1.5	30
90	Capacitanceâ€“conductance characteristics of Au/Ti/Al₂O₃/n-GaAs structures with very thin Al₂O₃interfacial layer. Materials Research Express, 2015, 2, 046301.	0.8	30

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91	Electrical characteristics of atomic layer deposited Au/Ti/HfO2/n-GaAs MIS diodes in the wide temperature range. Journal of Materials Science: Materials in Electronics, 2020, 31, 7839-7849.	1.1	30
92	Influence of interface states on the temperature dependence and currentâ€“voltage characteristics of Ni/p-InP Schottky diodes. Superlattices and Microstructures, 2010, 47, 241-252.	1.4	29
93	Effect of temperature on the capacitanceâ€“frequency and conductanceâ€“voltage characteristics of polyaniline/p-Si/Al MIS device at high frequencies. Microelectronics Reliability, 2012, 52, 1362-1366.	0.9	29
94	Temperature-dependent electrical characteristics of Alq3/p-Si heterojunction. Physica B: Condensed Matter, 2018, 550, 68-74.	1.3	29
95	The effects of the temperature on currentâ€“voltage characteristics of Sn/polypyrrole/n-Si structures. Synthetic Metals, 2005, 150, 15-20.	2.1	28
96	Temperature-dependent currentâ€“voltage characteristics of Cr/n-GaAs Schottky diodes. Microelectronic Engineering, 2009, 86, 111-116.	1.1	28
97	The current-voltage characteristics of the ferroelectric p-YMnO3 thin film/bulk p-Si heterojunction over a broad measurement temperature range. Journal of Alloys and Compounds, 2019, 782, 566-575.	2.8	28
98	The Cu/n-GaAs schottky barrier diodes prepared by anodization process. Journal of Electronic Materials, 2002, 31, 1362-1368.	1.0	27
99	Barrier height enhancement and stability of the Auâˆ•n-InP Schottky barrier diodes oxidized by absorbed water vapor. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 2436.	1.6	27
100	Determination of the laterally homogeneous barrier height of thermally annealed and unannealed Au/p-InP/Zn-Au Schottky barrier diodes. Applied Surface Science, 2008, 254, 3558-3561.	3.1	27
101	Thermally annealed Ni/n-GaAs(Si)/In Schottky barrier diodes. Microelectronic Engineering, 2008, 85, 655-658.	1.1	27
102	Capacitance-conductance-frequency characteristics of Au/Ni/n-GaN/undoped GaN Structures. Physica B: Condensed Matter, 2015, 457, 48-53.	1.3	27
103	An investigation of the optical properties of YbFe1-xIrxO3-áºŸ (x=0, 0.01 and 0.10) orthoferrite films. Vacuum, 2020, 173, 109124.	1.6	27
104	Examination of optical properties of YbFeO3 films via doping transition element osmium. Optical Materials, 2020, 105, 109911.	1.7	27
105	Current-voltage-temperature analysis of inhomogeneous Au/n-GaAs Schottky contacts. EPJ Applied Physics, 2005, 31, 79-86.	0.3	26
106	The barrier-height inhomogeneity in identically prepared Ni/n-type 6H-SiC Schottky diodes. Applied Physics A: Materials Science and Processing, 2008, 91, 337-340.	1.1	26
107	Capacitance and conductanceâ€“frequency characteristics of Auâ€“Sb/p-GaSe:Gd Schottky barrier diode. Vacuum, 2011, 85, 798-801.	1.6	26
108	Determination of the some electronic parameters of nanostructure copper selenide and Cu/Cu3Se2/n-GaAs/In structure. Journal of Alloys and Compounds, 2015, 627, 200-205.	2.8	26

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109	Tailoring the band gap of ferroelectric YMnO3 through tuning the Os doping level. Journal of Materials Science: Materials in Electronics, 2019, 30, 3443-3451.	1.1	26
110	The barrier-height inhomogeneity in identically prepared H-terminated Ti/p-Si Schottky barrier diodes. Semiconductor Science and Technology, 2004, 19, 1113-1116.	1.0	25
111	Currentâ€“voltage characteristics of Al/Rhodamine-101/n-GaAs and Cu/Rhodamine-101/n-GaAs rectifier contacts. Synthetic Metals, 2007, 157, 679-683.	2.1	25
112	The electrical measurements in poly(2-chloroaniline) based thin film sandwich devices. Thin Solid Films, 2007, 515, 7253-7258.	0.8	25
113	Determination of the laterally homogeneous barrier height of metal/p-InP Schottky barrier diodes. Vacuum, 2009, 83, 1470-1474.	1.6	25
114	Extraction of electronic parameters of Schottky diode based on an organic Indigotindisulfonate Sodium (IS). Solid State Communications, 2010, 150, 1592-1596.	0.9	25
115	Effect of Os doping on electrical properties of YMnO3 multiferroic perovskite-oxide compounds. Materials Science in Semiconductor Processing, 2019, 91, 281-289.	1.9	25
116	The effects of the ageing on the characteristic parameters of polyaniline/p-type Si/Al structure. Applied Surface Science, 2004, 230, 404-410.	3.1	24
117	Electrical characteristics of the hydrogen pre-annealed Au/n-GaAs Schottky barrier diodes as a function of temperature. Applied Surface Science, 2007, 253, 7246-7253.	3.1	24
118	The theoretical and experimental study on double-Gaussian distribution in inhomogeneous barrier-height Schottky contacts. Microelectronic Engineering, 2010, 87, 2225-2229.	1.1	24
119	The electrical characterizations and illumination response of Co/N-type GaP junction device. Current Applied Physics, 2015, 15, 1054-1061.	1.1	24
120	Electrical and photovoltaic properties of Ag/p-Si structure with GO doped NiO interlayer in dark and under light illumination. Journal of Alloys and Compounds, 2017, 718, 75-84.	2.8	24
121	THE CURRENTâ€“VOLTAGE CHARACTERISTICS OVER THE MEASUREMENT TEMPERATURE OF 60â€“400ÂK IN THE Au/Ti/n-GaAs CONTACTS WITH HIGH DIELECTRIC HfO₂ INTERFACIAL LAYER. Surface Review and Letters, 2019, 26, 1950045.	0.5	24
122	Electrical characteristics of Au/Ti/HfO2/n-GaAs metal-insulator-semiconductor structures with high-k interfacial layer. International Journal of Chemistry and Technology, 2018, 2, 116-122.	0.8	24
123	Metallic polythiophene/inorganic semiconductor Schottky diodes. Physica B: Condensed Matter, 1993, 192, 279-283.	1.3	23
124	Determination of lateral barrier height of identically prepared Ni/n-type Si Schottky barrier diodes by electrodeposition. Physica B: Condensed Matter, 2008, 403, 2211-2214.	1.3	23
125	Temperature-dependent Schottky barrier inhomogeneity of Ni/n-GaAs diodes. EPJ Applied Physics, 2009, 45, 10302.	0.3	23
126	Effect of hydrostatic pressure on the characteristic parameters of Au/n-GaAs Schottky-barrier diodes. Physical Review B, 1999, 60, 15944-15947.	1.1	22

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127	Temperature-dependent C-V characteristics of Au/ZnO/n-Si device obtained by atomic layer deposition technique. Journal of Materials Science: Materials in Electronics, 2017, 28, 5880-5886.	1.1	22
128	An experimental investigation: The impact of cobalt doping on optical properties of YbFeO3-á°Ÿ thin film. Materials Research Bulletin, 2019, 119, 110567.	2.7	22
129	The influence of cobalt (Co) doping on the electrical and dielectric properties of LaCr1-xCoxO3 perovskite-oxide compounds. Materials Science in Semiconductor Processing, 2020, 109, 104923.	1.9	22
130	Fabrication and electrical properties of organic-on-inorganic Schottky devices. Journal of Physics Condensed Matter, 2008, 20, 215210.	0.7	21
131	Fabrication and electrical characterization of a silicon Schottky device based on organic material. Physica Scripta, 2009, 79, 035802.	1.2	21
132	Linear correlation between barrier heights and ideality factors of Sn/n-Si schottky diodes with and without the interfacial native oxide layer. Physica B: Condensed Matter, 2003, 337, 388-393.	1.3	20
133	Prediction of lateral barrier height in identically prepared Ni/n-type GaAs Schottky barrier diodes. Applied Surface Science, 2007, 253, 7467-7470.	3.1	20
134	Barrier height temperature coefficient in ideal Ti/n-GaAs Schottky contacts. Microelectronic Engineering, 2010, 87, 1781-1784.	1.1	20
135	Evaluation of lateral barrier height of inhomogeneous photolithography-fabricated Au/n-GaAs Schottky barrier diodes from 80K to 320K. Materials Science in Semiconductor Processing, 2012, 15, 480-485.	1.9	20
136	Origin of forward bias capacitance peak and intersection behavior of C and G/w of Ag/p-InP Schottky barrier diodes. Materials Science in Semiconductor Processing, 2013, 16, 344-351.	1.9	20
137	The comparison of electrical characterizations and photovoltaic performance of Al/p-Si and Al/Azure C/p-Si junctions devices. Synthetic Metals, 2015, 200, 66-73.	2.1	20
138	Synthesis and Characterization of Reduced Graphene Oxide/Rhodamine 101 (rGO-Rh101) Nanocomposites and Their Heterojunction Performance in rGO-Rh101/p-Si Device Configuration. Journal of Electronic Materials, 2018, 47, 329-336.	1.0	20
139	Effect of atomic-layer-deposited HfO2 thin-film interfacial layer on the electrical properties of Au/Ti/n-GaAs Schottky diode. Journal of Materials Science: Materials in Electronics, 2021, 32, 10209-10223.	1.1	20
140	The effect of thermal treatment on the characteristic parameters of Ni/-, Ti/- and NiTi alloy/n-GaAs Schottky diodes. Solid-State Electronics, 1999, 43, 521-527.	0.8	19
141	Low- and high-frequencyC-V characteristics of the contacts formed by sublimation of the nonpolymeric organic compound on p-type Si substrate. Physica Status Solidi A, 2004, 201, 3077-3086.	1.7	19
142	Determination of the characteristic parameters of Sn/n-GaAs/Alâ€“Ge Schottky diodes by a barrier height inhomogeneity model. Semiconductor Science and Technology, 2006, 21, 822-828.	1.0	19
143	Fabrication and electrical properties of Al/aniline green/n-Si/AuSb structure. Materials Science in Semiconductor Processing, 2008, 11, 53-58.	1.9	19
144	On the electrical characteristics of the Al/rhodamine-101/p-Si MS structure at low temperatures. Materials Science in Semiconductor Processing, 2014, 28, 135-143.	1.9	19

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145	The Characteristic Parameters of Ni/n-6H-SiC Devices Over a Wide Measurement Temperature Range. Silicon, 2017, 9, 395-401.	1.8	19
146	Conductance and capacitance-frequency characteristics of polypyrrole/p-type silicon structures. Journal of Polymer Science, Part B: Polymer Physics, 2003, 41, 1334-1338.	2.4	18
147	DNA-based organic-on-inorganic devices: Barrier enhancement and temperature issues. Microelectronic Engineering, 2008, 85, 2250-2255.	1.1	18
148	Reverse bias capacitanceâ€“voltage characteristics of Al/polyaniline/p-Si/Al structure as a function of temperature. Journal of Non-Crystalline Solids, 2008, 354, 4991-4995.	1.5	18
149	A theoretical analysis together with experimental data of inhomogeneous Schottky barrier diodes. Microelectronic Engineering, 2009, 86, 2270-2274.	1.1	18
150	Effect of temperature on the current (capacitance and conductance)â€“voltage characteristics of Ti/n-GaAs diode. Journal of Applied Physics, 2014, 116, .	1.1	18
151	Electronic parameters of MIS Schottky diodes with DNA biopolymer interlayer. Materials Science-Poland, 2015, 33, 593-600.	0.4	18
152	The impact of Ir doping on the electrical properties of YbFe1â^'xIrxO3 perovskite-oxide compounds. Journal of Materials Science: Materials in Electronics, 2020, 31, 1731-1744.	1.1	18
153	Thermal treatment of the MIS and intimate Ni/n-LEC GaAs Schottky barrier diodes. Applied Surface Science, 1998, 135, 350-356.	3.1	17
154	Determination of the Density Distribution of Interface States from High- and Low-Frequency Capacitance Characteristics of the Tin/Organic Pyronine-B/p-type Silicon Structure. ChemPhysChem, 2002, 3, 701.	1.0	17
155	The Conductance- and Capacitance-Frequency Characteristics of the Rectifying Junctions Formed by Sublimation of Organic Pyronine-B on p-Type Silicon. Journal of Solid State Chemistry, 2002, 168, 169-174.	1.4	17
156	Electrical characteristics and inhomogeneous barrier analysis of aniline green/p-Si heterojunctions. Journal of Materials Science: Materials in Electronics, 2008, 19, 986-991.	1.1	17
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